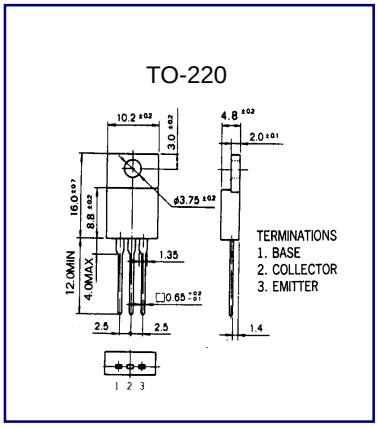
2SB595 PNP EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER



- Complement to 2SD525

ABSOLUTE MAXIMUM RATINGS (T_A=25℃)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base voltage	V_{EBO}	-5	V
Collector Current (DC)	I_C	-5	A
Collector Dissipation (Tc=25℃)	P_C	40	W
Junction Temperature	T_j	150	℃
Storage Temperature	Tstg	-50~150	℃

ELECTRICAL CHARACTERISTICS (T_A=25℃)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB}= -100V , I_E=0			-10	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=- 5V , I_C=0			10	μA
DC Current Gain	h_{FE1}	V_{CE}= -5V , I_C=-1A	40		320	
Collector- Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-4A , I_B=-0.4A			-2.0	V
Current Gain Bandwidth Product	f_T	V_{CE}= -5V , I_C=-0.5A		8		MHz

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